

Product data sheet

1. General description

Ultrafast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- Fast switching
- Guaranteed ESD capability
- High thermal cycling performance
- Low on-state loss
- Low thermal resistance
- Rugged: reverse voltage surge capability
- · Soft recovery minimizes power-consuming oscillations

3. Applications

• Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	100	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 128 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u>	-	-	8	A
Static charact	eristics	· · · · · · · · · · · · · · · · · · ·				
V _F	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	-	0.8	0.895	V
Dynamic char	acteristics	· · · · · · · · · · · · · · · · · · ·				
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ ramp recovery}; Fig. 5; Fig. 7$	-	20	25	ns
Electrostatic o	lischarge	· ·				
V _{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ	-	-	8	kV





5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	mb	K — A 001aaa020
2	А	anode	$2 \circ 4$	001aaa020
mb	mb	mounting base; cathode	C () () () () () () () () () ()	

6. Ordering information

Table 3. Ordering inf	formation					
Type number	Package					
	Name	Description	Version			
BYW29E-100	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59			

7. Limiting values

Table 4.Limiting values

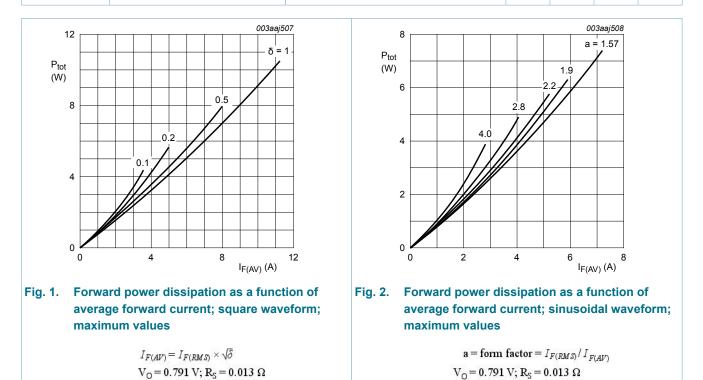
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{RRM}	repetitive peak reverse voltage		-	100	V
V _{RWM}	crest working reverse voltage		-	100	V
V _R	reverse voltage		-	100	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 128 °C; square-wave pulse; Fig. 1; Fig. 2	-	8	A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _{mb} ≤ 128 °C; square-wave pulse	-	16	A
I _{FSM}	non-repetitive peak forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	88	A
		t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	80	A
I _{RRM}	repetitive peak reverse current	δ = 0.001 ; t _p = 2 μs	-	0.2	Α

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Symbol	Parameter	Conditions		Min	Max	Unit	
I _{RSM}	non-repetitive peak reverse current	t _p = 100 μs		-	0.2	A	
T _{stg}	storage temperature			-40	150	°C	
Tj	junction temperature			-	150	°C	
Electrostatic discharge							
V _{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ		-	8	kV	

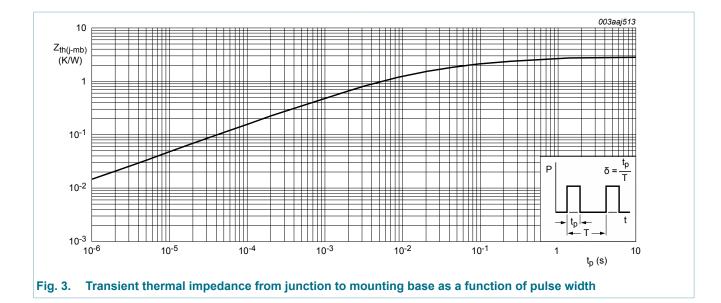


8. Thermal characteristics

Table 5. Thermal characteristics								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 3</u>		-	-	2.7	K/W	
R _{th(j-a)}	thermal resistance from junction to ambient	in free air		-	60	-	K/W	

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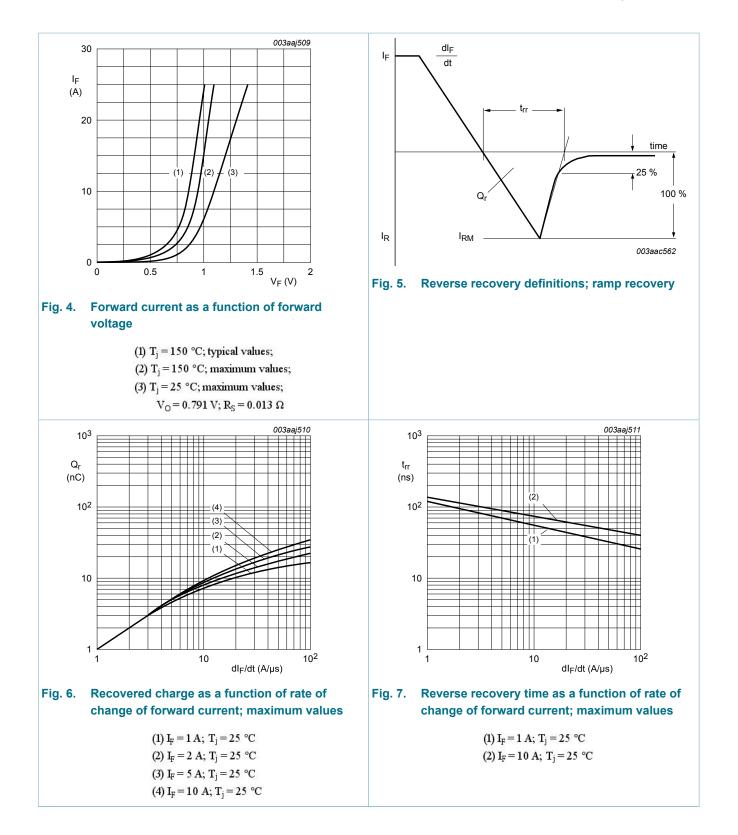


9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	acteristics	· · · ·				,
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 4</u>	-	0.92	1.05	V
		I _F = 20 A; T _j = 25 °C; <u>Fig. 4</u>	-	1.1	1.3	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	-	0.8	0.895	V
I _R	reverse current	V _R = 100 V; T _j = 25 °C	-	2	10	μA
		V _R = 100 V; T _j = 100 °C	-	0.2	0.6	mA
Dynamic cł	naracteristics	· · · ·				
Qr	recovered charge	$I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A}/\mu\text{s};$ T _j = 25 °C; Fig. 5; Fig. 6	-	4	11	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ ramp recovery}; Fig. 5; Fig. 7$	-	20	25	ns
		$I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_{R(meas)} = 0.25 \text{ A};$ T _j = 25 °C; step recovery; <u>Fig. 8</u>	-	15	20	ns
V _{FRM}	forward recovery voltage	I _F = 1 A; dI _F /dt = 10 A/μs; T _j = 25 °C; Fig. 9	-	1	-	V

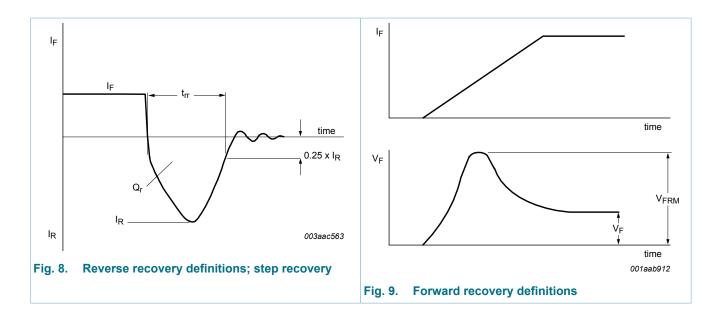
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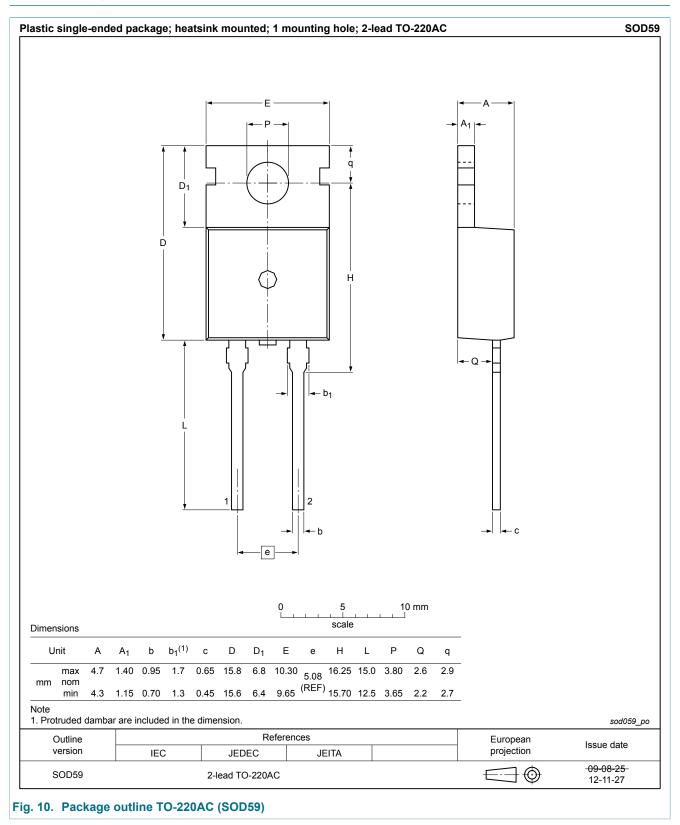
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10. Package outline



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11. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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